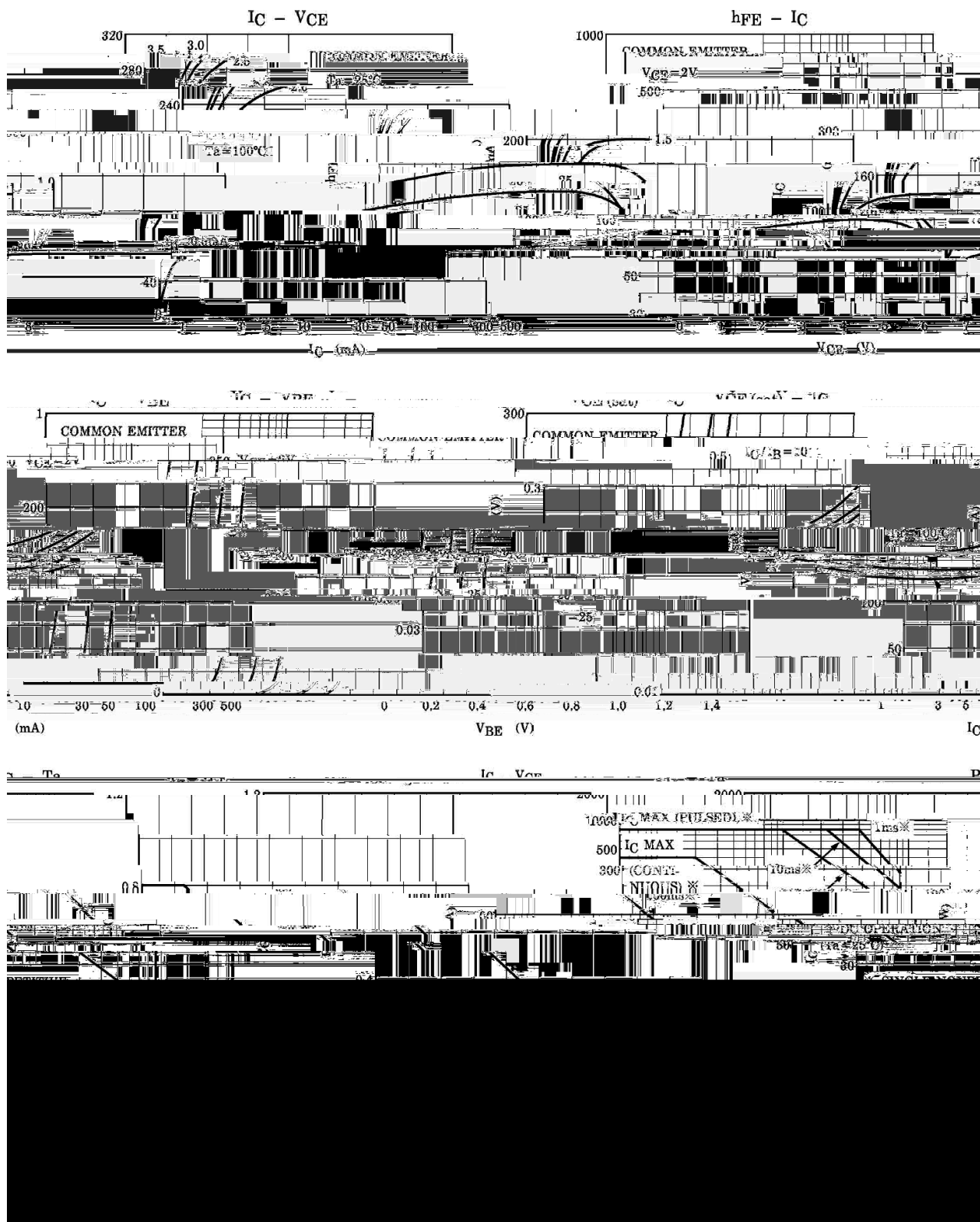


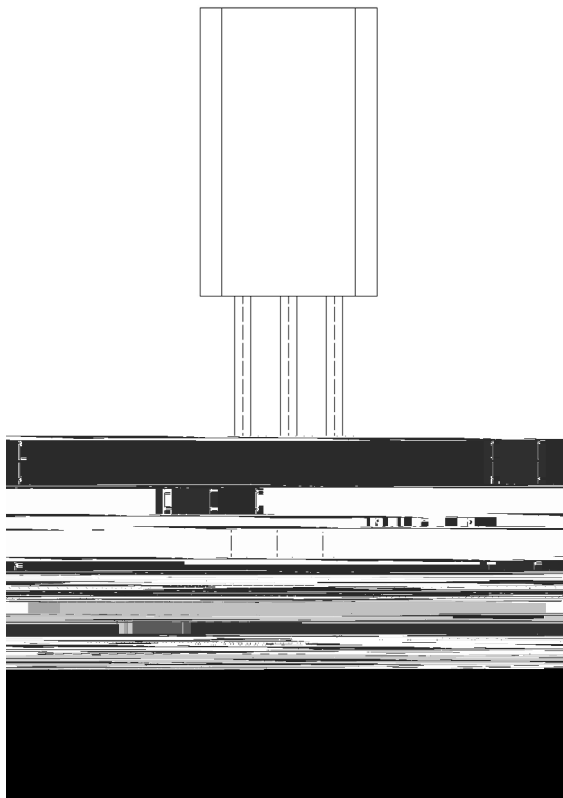
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	400	mA
Emitter Current – Continuous	I_E	-400	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=5.0mA$ $I_B=0$	80			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=50V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0V$ $I_C=50mA$	70		240	
	$h_{FE(2)}$	$V_{CE}=2.0V$ $I_C=200mA$	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA$ $I_B=20mA$			0.4	V

/ Electrical Characteristic Curve



/ Marking Instructions



б " X

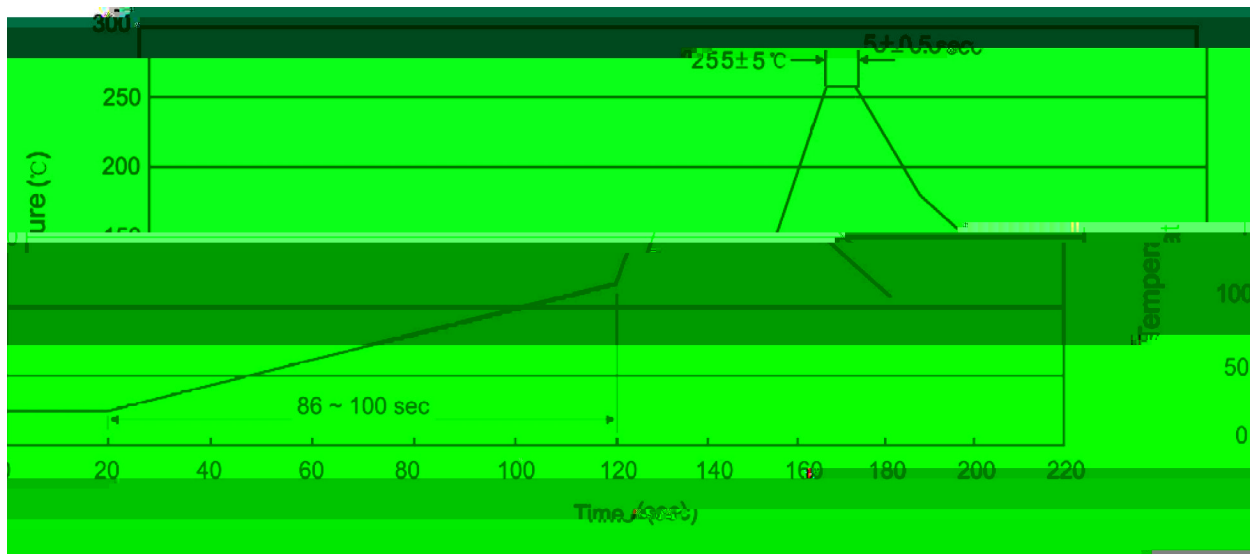
EU: № з " ПД

F495:D X № з " ПД

R: № k_{IH} ' ° ПД

RS f њ

() / Temperature Profile for Dip Soldering(Pb-Free)



说明

1. 预加热: 25~150℃, 时间: 60~90sec;
2. 峰值温度: 255±5℃, 持续时间: 5±0.5sec;
3. 冷却速度: 2~10℃/sec.

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 255±5℃, Duration: 5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

环境温度: 270±5℃, 时间: 10±1 sec.

Tf0.56D935.8(5(.7150))TJ/TT7 1 Tf314.9486 0